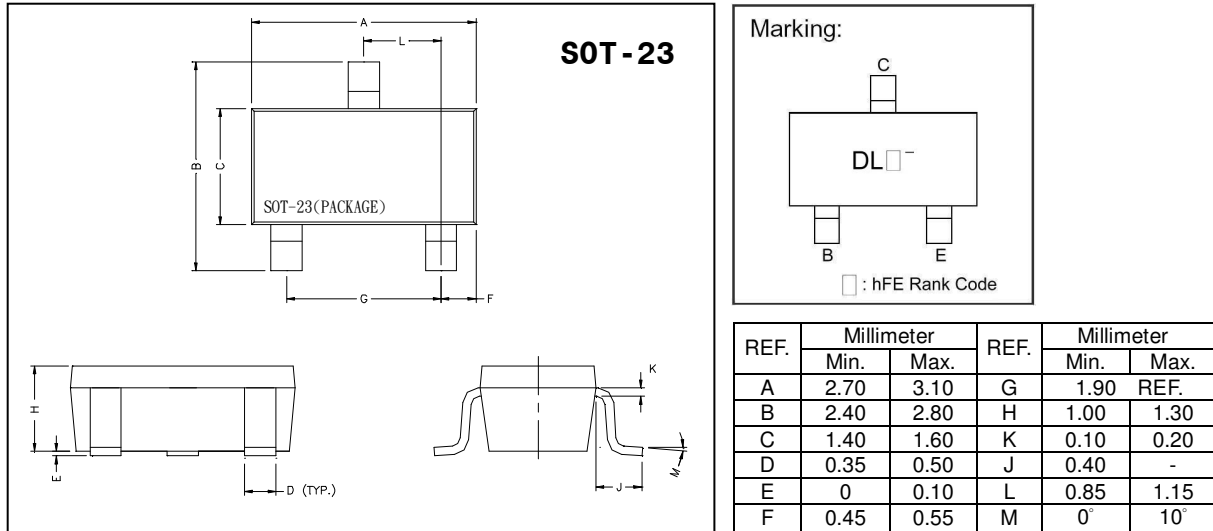


GMBT8050L NPN EPITAXIAL TRANSISTOR

Description

The GMBT8050L(large current) is designed for general purpose amplifier applications.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage	V _{CB0}	40	V
Collector to Emitter Voltage	V _{CE0}	25	V
Emitter to Base Voltage	V _{EB0}	6	V
Collector Current	I _C	1.5	A
Total Power Dissipation	P _D	250	mW

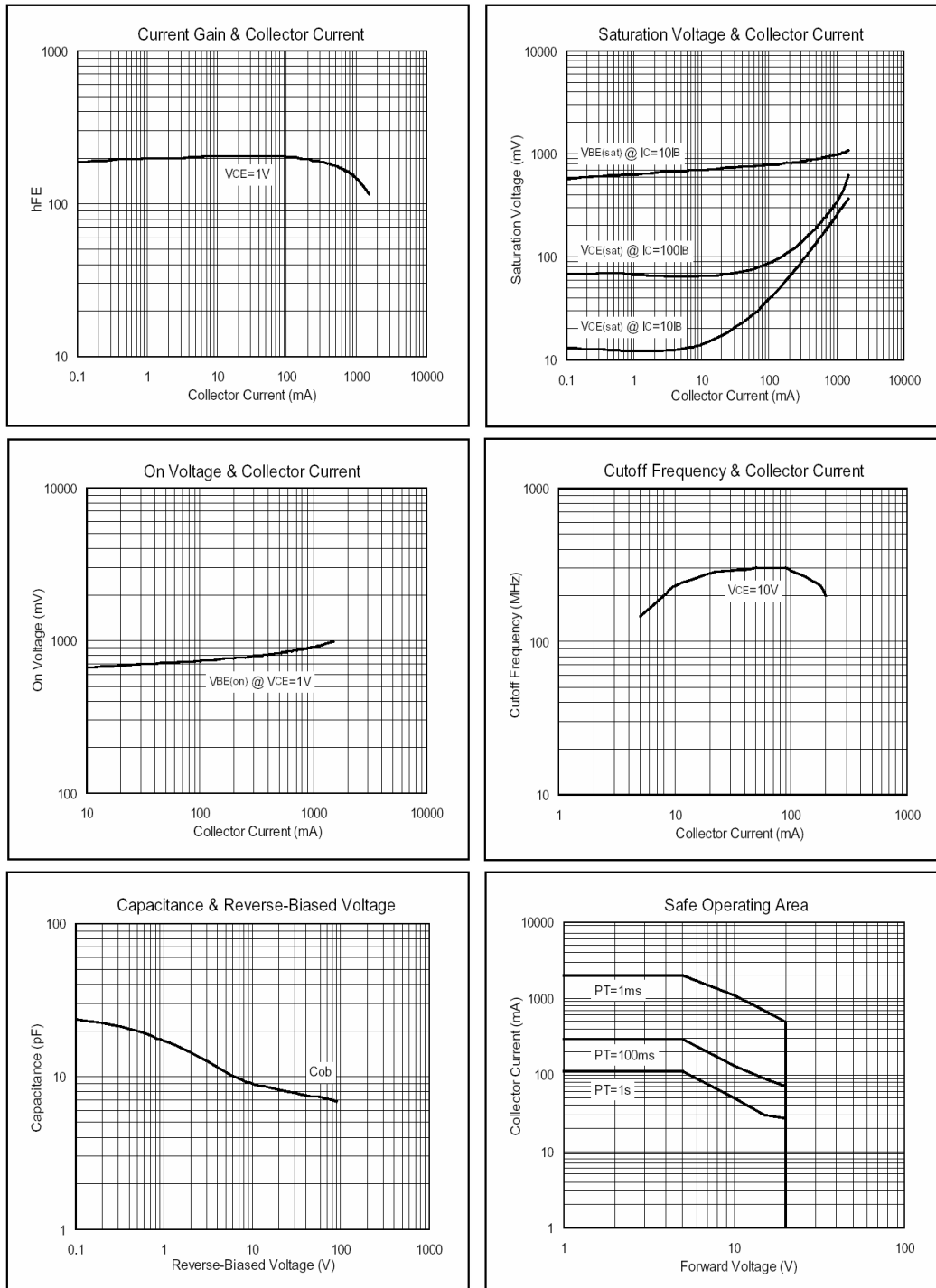
Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V _{CB0}	40	-	-	V	I _C =100uA, I _E =0
V _{CE0}	25	-	-	V	I _C =2mA, I _B =0
V _{EB0}	6	-	-	V	I _E =100uA, I _C =0
I _{CB0}	-	-	100	nA	V _{CB} =35V, I _E =0
I _{EB0}	-	-	100	nA	V _{EB} =6V, I _C =0
V _{CE(sat)}	-	-	0.5	V	I _C =800mA, I _B =80mA
V _{BE(sat)}	-	-	1.2	V	I _C =800mA, I _B =80mA
V _{BE(on)}	-	-	1	V	V _{CE} =1V, I _C =10mA
h _{FE}	45	-	-		V _{CE} =1V, I _C =5mA
h _{FE}	120	-	500		V _{CE} =1V, I _C =100mA
h _{FE}	40	-	-		V _{CE} =1V, I _C =800mA
f _T	100	-	-	MHz	V _{CE} =10V, I _C =20mA, f=100MHz
C _{ob}	-	-	10	pF	V _{CB} =10V, f=1MHz

Classification Of hFE

Rank	DLC	DLD	DLE
hFE	120 - 200	160 - 300	250 - 500

Characteristics Curve



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